TOSHIBA

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

MICROWAVE POWER GaN HEMT TGI1314-50L

FEATURES

■ HIGH POWER

Pout=47.0dBm at Pin=42.0dBm

■ HIGH GAIN
GL=8.0dB at 13.75GHz to 14.5GHz

■ BROAD BAND INTERNALLY MATCHED HEMT

HERMETICALLY SEALED PACKAGE

■ LOW INTERMODULATION DISTORTION

IM3(Min.)=–25dBc at Po=40.0dBm Single Carrier Level

RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power	Pout	\/DQ04\/	dBm	46.0	47.0	_
Gain Flatness	ΔG	VDS = 24V	dB	I	ı	±0.8
Drain Current	IDS1	IDSset≌2.0A f = 13.75 to 14.5GHz	Α	I	5.0	6.0
Power Added Efficiency	ηadd	@ Pin=42dBm	%	l	29	_
Gate Current	lg _{RF}	⊚ I III— T ZuDIII	mΑ	-40	_	+100
Linear Gain	GL	@Pin=20dBm	dB	7.0	8.0	_
3rd Order Intermodulation Distortion	IM3	Two-Tone Test Po= 40.0dBm	dBc	-25	_	_
Drain Current	IDS2	(Single Carrier Level)	Α	Ι	5.0	6.0
Channel Temperature Rise	∆Tch	(VDS X IDS + Pin – Pout) X Rth(c-c)	°C	_	130	150

Recommended gate resistance(Rg) : Rg= 13.3Ω (TYP.)

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

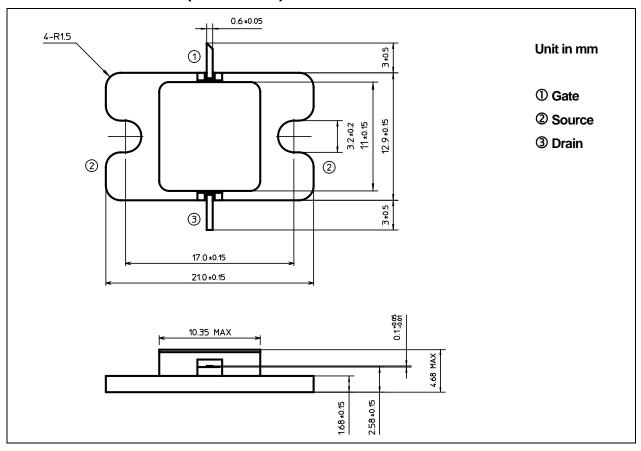
CHARACTERISTICS	SYMBOL	CONDITIONS		UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS=	5V	S	_	4.5	
		IDS=	5.0A				
Pinch-off Voltage	VGSoff	VDS=	5V	V	-1	-4	-6
		IDS=	23mA				
Saturated Drain Current	IDSS	VDS=	5V	Α		15	
		VGS=	0V				
Gate-Source Breakdown	VGSO	IGS=	-10mA	V	-10		
Voltage							
Thermal Resistance	Rth(c-c)	Channel to Case		°C/W	_		1.6

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ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	50
Gate-Source Voltage	VGS	V	-10
Drain Current	IDS	Α	15
Total Power Dissipation (Tc= 25 °C)	PT	W	140
Channel Temperature	Tch	°C	250
Storage	Tstg	°C	-65 to +175

PACKAGE OUTLINE (7- AA07A)



HANDLING PRECAUTIONS FOR PACKAGE MODEL

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C.